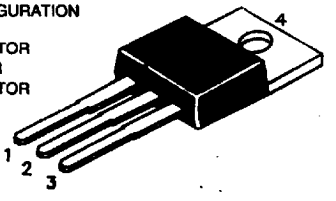
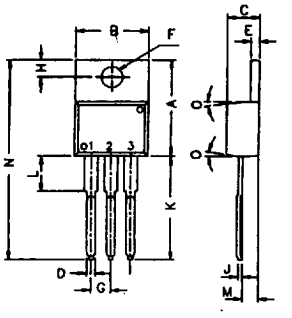
CSA940 PNP PLASTIC POWER TRANSISTOR
CSC2073 NPN PLASTIC POWER TRANSISTOR

Power Amplifier Applications and Vertical Output Applications

PIN CONFIGURATION
1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR





ALL DIMENSIONS ARE IN M.M.

DIM	MIN	MAX
A	14,42	16,51
B	9,63	10,67
C	3,56	4,83
D	–	0,90
E	1,15	1,40
F	3,75	3,88
G	2,29	2,79
H	2,54	3,43
J	–	0,56
K	12,70	14,73
L	–	6,35
M	2,03	2,92
N	–	31,24
O	7 DEG	

ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	V_{CBO}	max.	150 V
Collector-emitter voltage (open base)	V_{CEO}	max.	150 V
Collector current	I_C	max.	1.5 A
Total power dissipation up to T_C = 25°C	P_{tot}	max.	25 W
Junction temperature	T_j	max.	150 °C
Collector-emitter saturation voltage			
I_C = 500 mA; I_B = 50 mA	V_{CEsat}	max.	1.5 V
D.C. current gain			
I_C = 500 mA; V_{CE} = 10 V	h_{FE}	min.	40
		max.	140

RATINGS (at T_A=25°C unless otherwise specified)

Limiting values			
Collector-base voltage (open emitter)	V_{CBO}	max.	150 V
Collector-emitter voltage (open base)	V_{CEO}	max.	150 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5.0 V

Collector current	I_C	max.	1.5 A
Base current	I_B	max.	0.5 A
Total power dissipation up to T_C = 25°C	P_{tot}	max.	25 W
Total power dissipation up to T_A = 25°C	P_{tot}	max.	1.5 W
Junction temperature	T_j	max.	150 °C
Storage temperature	T_{stg}	−65 to +150	°C

CHARACTERISTICS

T_{amb} = 25°C unless otherwise specified

Collector cutoff current			
I_E = 0; V_{CB} = 120 V	I_{CBO}	max.	10 µA
Emitter cut-off current			
I_C = 0; V_{EB} = 5 V	I_{EBO}	max.	10 µA
Breakdown voltages			
I_C = 1 mA; I_B = 0	V_{CEO}	min.	150 V
I_C = 1 mA; I_E = 0	V_{CBO}	min.	150 V
I_E = 1 mA; I_C = 0	V_{EBO}	min.	5.0 V
Saturation voltages			
I_C = 500 mA; I_B = 50 mA	V_{CEsat}	max.	1.5 V
Base emitter on voltage			
I_C = 500 mA; V_{CE} = 10 V	$V_{BE(on)}$	min.	0.65 V
		max.	0.85 V
D.C. current gain			
I_C = 500 mA; V_{CE} = 10 V	h_{FE}	min.	40
		max.	140
Output capacitance at f = 1 MHz			
I_E = 0; V_{CB} = 10 V NPN	C_o	typ.	35 pF
PNP		typ.	55 pF
Transition frequency			
I_C = 500 mA; V_{CE} = 10 V	f_T	typ.	4 MHz